NPN - MPS650, MPS651; PNP - MPS750, MPS751

Amplifier Transistors

Features

• These are Pb-Free Devices*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage MPS650; MPS750 MPS651; MPS751	V _{CE}	40 60	Vdc
Collector – Base Voltage MPS650; MPS750 MPS651; MPS751	V _{CB}	60 80	Vdc
Emitter – Base Voltage	V _{EB}	5.0	Vdc
Collector Current – Continuous	Ι _C	2.0	Adc
Total Power Dissipation @ T _A = 25°C Derate above 25°C	PD	625 5.0	mW mW/°C
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

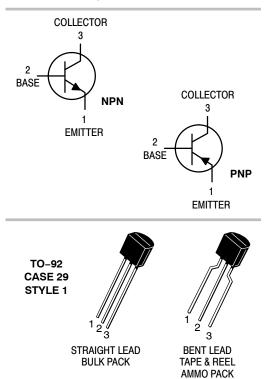
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	V _{CE}	200	°C/W
Thermal Resistance, Junction-to-Case	V _{CB}	83.3	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

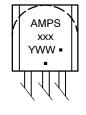


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MARKING DIAGRAM



 xxx
 = 650, 750, 651, or 751

 A
 = Assembly Location

 Y
 = Year

 WW
 = Work Week

 •
 = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

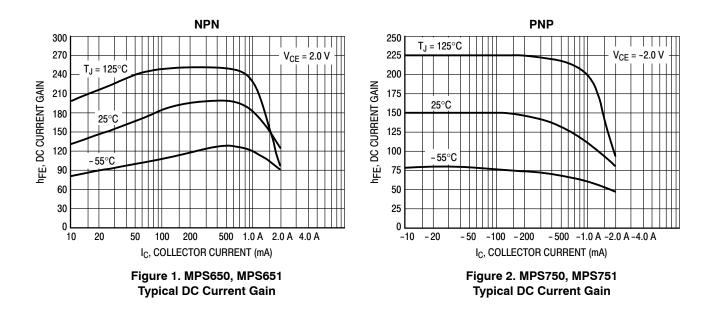
NPN - MPS650, MPS651; PNP - MPS750, MPS751

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

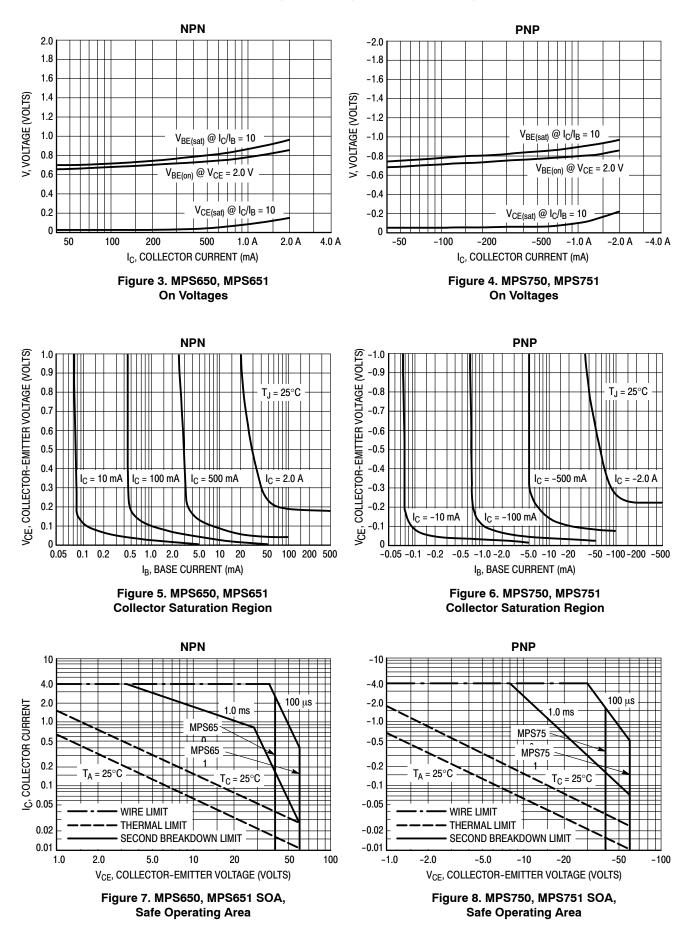
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (Note 1) ($I_C = 10 \text{ mAdc}, I_B = 0$)	MPS650, MPS750 MPS651, MPS751	V _{(BR)CEO}	40 60		Vdc
Collector – Base Breakdown Voltage ($I_C = 100 \ \mu Adc, I_E = 0$)	MPS650, MPS750 MPS651, MPS751	V _{(BR)CBO}	60 80		Vdc
Emitter – Base Breakdown Voltage $(I_C = 0, I_E = 10 \ \mu Adc)$		V _{(BR)EBO}	5.0	-	Vdc
Collector Cutoff Current $(V_{CB} = 60 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 80 \text{ Vdc}, I_E = 0)$	MPS650, MPS750 MPS651, MPS751	I _{CBO}		0.1 0.1	μAdc
Emitter Cutoff Current ($V_{EB} = 4.0 \text{ V}, I_C = 0$)		I _{EBO}	-	0.1	μAdc
ON CHARACTERISTICS (Note 1)			•		
$ \begin{array}{l} \text{DC Current Gain} \\ (I_C = 50 \text{ mA}, \text{V}_{CE} = 2.0 \text{ V}) \\ (I_C = 500 \text{ mA}, \text{V}_{CE} = 2.0 \text{ V}) \\ (I_C = 1.0 \text{ A}, \text{V}_{CE} = 2.0 \text{ V}) \\ (I_C = 2.0 \text{ A}, \text{V}_{CE} = 2.0 \text{ V}) \end{array} $		h _{FE}	75 75 75 40	- - - -	_
Collector – Emitter Saturation Voltage ($I_C = 2.0 \text{ A}, I_B = 200 \text{ mA}$) ($I_C = 1.0 \text{ A}, I_B = 100 \text{ mA}$)		V _{CE(sat)}		0.5 0.3	Vdc
Base–Emitter On Voltage (I _C = 1.0 A, V _{CE} = 2.0 V)		$V_{BE(on)}$	-	1.0	Vdc
Base – Emitter Saturation Voltage (I _C = 1.0 A, I _B = 100 mA)		V _{BE(sat)}	-	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS	I			I	1
Current – Gain – Bandwidth Product (Note 2) (I _C = 50 mAdc, V _{CE} = 5.0 Vdc, f = 100 MHz)		f _T	75	-	MHz

1. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle = 2.0%.

2. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.



NPN - MPS650, MPS651; PNP - MPS750, MPS751



NPN – MPS650, MPS651; PNP – MPS750, MPS751

ORDERING INFORMATION

Device	Package	Shipping [†]	
MPS650G	TO-92 (Pb-Free)	5000 Units / Bulk	
MPS650RLRAG	TO–92 (Pb–Free)	2000 / Tape & Reel	
MPS650ZL1G	TO–92 (Pb–Free)	2000 / Tape & Ammunition	
MPS651G	TO–92 (Pb–Free)	5000 Units / Bulk	
MPS651RLRAG	TO–92 (Pb–Free)	2000 / Tape & Reel	
MPS651RLRMG	TO–92 (Pb–Free)	2000 / Tape & Ammunition	
MPS750G	TO–92 (Pb–Free)	5000 Units / Bulk	
MPS750RLRAG	TO–92 (Pb–Free)	2000 / Tape & Reel	
MPS750RLRPG	TO–92 (Pb–Free)	2000 / Tape & Ammunition	
MPS751G	TO–92 (Pb–Free)	5000 Units / Bulk	
MPS751RLRAG	TO–92 (Pb–Free)	2000 / Tape & Reel	
MPS751RLRPG	TO–92 (Pb–Free)	2000 / Tape & Ammunition	
MPS751ZL1G	TO–92 (Pb–Free)	2000 / Tape & Ammunition	

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM** NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI STRAIGHT LEAD B Y14.5M, 1982. CONTROLLING DIMENSION: INCH. **BULK PACK** 2 CONTOUR OF PACKAGE BEYOND DIMENSION R 3. IS UNCONTROLLED. LEAD DIMENSION IS UNCONTROLLED IN P AND 4. P BEYOND DIMENSION K MINIMUM. L INCHES MILLIMETERS SEATING κ DIM MIN MAX MIN MAX A 0.175 0.205 4.45 5.20 **B** 0.170 0.210 4.32 5.33 C 0.165 0.125 3.18 4.19 **D** 0.016 0.021 0.407 0.533 D G 0.045 0.055 1.15 1.39 H 0.095 0.105 2.42 2.66 G J 0.015 0.020 0.39 0.50 K 0.500 12.70 L 0.250 6.35 N 0.080 C 0.105 2.04 2.66 Ρ 0.100 2.54 SECTION X-X R 0.115 2.93 V 0.135 3.43 NOTES: BENT LEAD DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. В R 1. TAPE & REEL CONTROLLING DIMENSION: MILLIMETERS. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED. AMMO PACK 3. 4 LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM. P T SEATING PLANE MILLIMETERS DIM MIN MAX A 4.45 5.20 в 4.32 5.33 С 3.18 4.19 D 0.40 0.54 n G 2 40 2 80 G J 0.39 0.50 K 12.70 Ν 2.04 2 66 Ρ 1.50 4.00 C R 2.93 SECTION X-X 3.43 STYLE 1: PIN 1. EMITTER BASE 2. COLLECTOR 3.

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